PENDING CLAIMS

The following is a list of currently pending claims. No claims are added, amended, or deleted in this response.

- (Original) A method for depositing a doped polysilicon film comprising:
 providing a surface; and
 substantially simultaneously flowing SiH₄ and BCl₃ over the surface at a
 temperature less than or equal to about 500 degrees Celsius under conditions
 that achieve an average concentration in the doped polysilicon film of
 between about 7 x 10²⁰ and about 3 x 10²¹ boron atoms per cubic centimeter.
- (Original) The method of claim 1 wherein the temperature is between about 450 and about 480 degrees Celsius.
- 3. (Original) The method of claim 2 wherein pressure is between about 200 mTorr and about 1 Torr.
- 4. (Original) The method of claim 3 wherein an inert gas is flowed over the surface with the SiH₄ and BCl₃.
- 5. (Original) The method of claim 4 wherein the inert gas is helium.
- 6. (Original) A method for forming in-situ doped polysilicon comprising: providing a surface; and substantially simultaneously flowing a first source gas comprising SiH₄ and a second source gas comprising BCl₃ over the surface at a temperature less than about 500 degrees Celsius under conditions sufficient to achieve in the doped polysilicon an average concentration of between about 7 x 10²⁰ and about 3 x 10²¹ boron atoms per cubic centimeter.

- 7. (Original) The method of claim 6, wherein the second source gas comprises about 0.1 percent BCl₃ or more.
- 8. (Original) The method of claim 7, wherein the second source gas further comprises an inert gas.
- (Original) The method of claim 8, wherein the temperature is between about 450 and about 480 degrees Celsius.
- 10. (Original) The method of claim 9, wherein the inert gas is helium.
- 11. (Original) The method of claim 8, wherein the pressure is between about 200 mTorr and about 1 Torr.
- 12. (Original) A method for depositing in-situ doped polysilicon comprising:

 providing a substrate comprising a substantially horizontal surface and a
 substantially vertical sidewall descending from the horizontal surface, the
 sidewall having a top; and
 - depositing an in-situ doped polysilicon film on the surface at a temperature less than about 500 degrees Celsius, wherein:
 - a first thickness of the film at its thinnest point on the vertical sidewall is at least 80 percent of a second thickness of the film on the sidewall at the top of the sidewall, and
 - a third thickness of the film on the horizontal surface is at least 200 angstroms.
- 13. (Original) The method of claim 12 wherein the step of depositing the polysilicon film comprises substantially simultaneously flowing SiH₄ and BCl₃ over the surface.
- 14. (Original) The method of claim 13 wherein an average concentration of boron atoms in the polysilicon is between about 7 x 10²⁰ and about 3 x 10²¹ per cubic centimeter.

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- 15. (Original) The method of claim 14 wherein the temperature is between about 450 and about 480 degrees Celsius.
- 16. (Original) The method of claim 15 wherein the pressure is between 200 mTorr and 1 Torr.